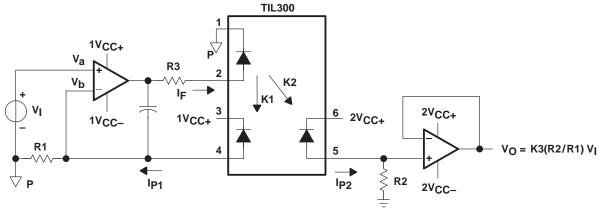
- ac or dc Signal Coupling
- Wide Bandwidth . . . > 200 kHz
- High Transfer-Gain Stability . . . ±0.05%/°C
- 3500 V Peak Isolation
- UL Approval Pending
- Applications
  - Power-Supply Feedback
  - Medical-Sensor Isolation
  - Opto Direct-Access Arrangement (DAA)
  - Isolated Process-Control Transducers

#### 

## description

The TIL300 precision linear optocoupler consists of an infrared LED irradiating an isolated feedback photodiode and an output photodiode in a bifurcated arrangement. The feedback photodiode captures a percentage of the flux of the LED and generates a control signal that can be used to regulate the LED drive current. This technique is used to compensate for the nonlinear time and temperature characteristics of the LED. The output-side photodiode produces an output signal that is linearly proportional to the servo-optical flux emitted from the LED.

A typical application circuit (shown in Figure 1) uses an operational amplifier as the input to drive the LED. The feedback photodiode sources current through R1, which is connected to the inverting input of the input operational amplifier. The photocurrent  $I_{P1}$  assumes a magnitude that satisfies the relationship  $I_{P1} = V_I/R1$ . The magnitude of the current is directly proportional to the LED current through the feedback transfer gain  $K1(V_I/R1 = K1 \times I_F)$ . The operational amplifier supplies LED current to produce sufficient photocurrent to keep the node voltage  $V_b$  equal to node voltage  $V_a$ .



NOTES: A. K1 is servo current gain, the ratio of the feedback photodiode current (IP1) to the input LED current (IF), i.e. K1 = IP1/IF.

- B. K2 is forward gain, the ratio of the output photodiode current ( $Ip_2$ ) to the input LED current ( $Ip_1$ ), i.e.  $K2 = Ip_2/Ip_1$
- C. K3 is transfer gain, the ratio of the forward gain to the servo gain, i.e. K3 = K2/K1.

Figure 1. Typical Application Circuit



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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## **Terminal Functions**

TERMINAL		1/0	DESCRIPTION					
NAME	NO.	1/0	DESCRIPTION					
LEDK	1		LED cathode					
LEDA	2		LED anode					
PDK1	3		Photodiode 1 cathode					
PDA1	4		Photodiode 1 anode					
PDA2	5		Photodiode 2 anode					
PDK2	6		Photodiode 2 cathode					
NC	7		No internal connection					
NC	8		No internal connection					

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Emitter	
Continuous total power dissipation (see Note 1)	160 mW
Input LED forward current, I <sub>F</sub>	
Surge current with pulse width < 10 μs	250 mA
Reverse voltage, V <sub>R</sub>	
Reverse current, I <sub>R</sub>	
Detector	
Continuous power dissipation (see Note 2)	50 mW
Reverse voltage, V <sub>R</sub>	50 V
Coupler	

Coupler	
Continuous total power dissipation (see Note 3)	
Storage temperature, T <sub>stg</sub>	–55°C to 150°C
Operating temperature, T <sub>A</sub>	–55°C to 100°C
Input-to-output voltage	3535 Vpeak
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Derate linearly from 25°C at a rate of 2.66 mW/°C.
  - 2. Derate linearly from 25°C at a rate of 0.66 mW/°C.
  - 3. Derate linearly from 25°C at a rate of 3.33 mW/°C.

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# electrical characteristics at $T_A = 25$ °C

## **Emitter**

PARAMETER		CC	CONDITIONS			MAX	UNIT
٧F	Forward voltage	I <sub>F</sub> = 10 mA			1.25	1.50	V
	Temperature coefficient of V <sub>F</sub>				-2.2		mV/°C
$I_R$	Reverse current	V <sub>R</sub> = 5 V				10	μΑ
t <sub>r</sub>	Rise time	$I_F = 10 \text{ mA},$	$\Delta I_F = 2 \text{ mA}$		1		μs
t <sub>f</sub>	Fall time	I <sub>F</sub> = 10 mA,	$\Delta I_F = 2 \text{ mA}$		1		μs
Cj	Junction capacitance	V <sub>F</sub> = 0,	f = 1 MHz		15		pF

### Detector

PARAMETER		CONDITIONS		MIN	TYP <sup>†</sup>	MAX	UNIT
I <sub>DK</sub> †	Dark current	V <sub>R</sub> = 15 V,	IF = 0			25	nA
	Open circuit voltage	I <sub>F</sub> = 10 mA			0.5		V
los	Short circuit current limit	I <sub>F</sub> = 10 mA			80		μΑ
Ci	Junction capacitance	$V_F = 0$ ,	f = 1 MHz		12		рF

### Coupler

	PARAMETER		CONDITION	MIN	TYP	MAX	UNIT	
174 <sup>†</sup>	Sonyo current gain			I <sub>F</sub> = 1 mA	0.3%	0.7%	1.5%	
K1‡ Servo current gain				IF = 10 mA	0.5%	1.25%	2%	
K2§	Forward current gain		1	I <sub>F</sub> = 1 mA	0.3%	0.7%	1.5%	
K23	Torward current gain	_	Detector bias	$I_F = 10 \text{ mA}$	0.5%	1.25%	2%	
кз¶	Transfer gain	TIL300	voltage = -15 V	$I_F = 1 \text{ mA}$	0.75	1	1.25	
				I <sub>F</sub> = 10 mA	0.75	1	1.25	
K91		TIL300A		IF = 1 mA	0.9	1	1.10	
				I <sub>F</sub> = 10 mA	0.9	1	1.10	
	Coin towns return coefficient	K1/K2	I- 10 mA			-0.5		%/°C
	Gain temperature coefficient	K3	I <sub>F</sub> = 10 mA		±0.005			
.Vo#	Transfer gain linearity		I <sub>F</sub> = 1 to 10 mA			±0.25%		
∆K3 <sup>#</sup>			$I_F = 1$ to 10 mA,	$T_A = 0 \text{ to } 75^{\circ}\text{C}$		±0.5%		
BW	Bandwidth		$I_F = 10 \text{ mA},$ $I_F(MODULATION) = \pm 2 \text{ mA}$	$R_L = 1 \text{ k}\Omega$ ,		200		kHz
t <sub>r</sub>	Rise time		$I_F = 10 \text{ mA},$ $I_F(MODULATION) = \pm 2 \text{ mA}$	$R_L = 1 \text{ k}\Omega$ ,		1.75		μs
t <sub>f</sub>	Fall time		$I_F = 10 \text{ mA},$ $I_F(MODULATION) = \pm 2 \text{ mA}$	$R_L = 1 k\Omega$ ,		1.75		μs
v <sub>iso</sub> †	Peak Isolation voltage		I <sub>IO</sub> = 10 μA, time = 1 minute	f = 60 Hz	3535		·	V

<sup>†</sup>This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.



<sup>‡</sup> Servo current gain (K1) is the ratio of the feedback photodiode current (I<sub>P1</sub>) to the input LED current (I<sub>F</sub>) current (I<sub>F</sub>), i.e. K1 = I<sub>P1</sub>/I<sub>F</sub>.

<sup>§</sup> Forward gain (K2 is the ratio of the output photodiode current (Ip2) to the input LED current (Ip), i.e.  $K2 = Ip2/I_F$ .

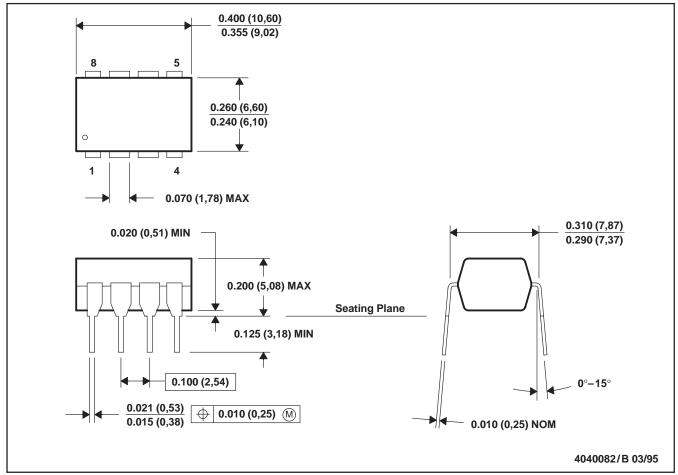
<sup>¶</sup> Transfer gain (K3) is the ratio of the forward gain to the servo gain, i.e. K3 = K2/K1.

<sup>#</sup> Transfer gain linearity (ΔK3) is the percent deviation of the transfer gain K3 as a function of LED input current (I<sub>F</sub>) or the package temperature.

## **MECHANICAL DATA**

## P (R-PDIP-T8)

## PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

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